

TOSHIBA Transistor Silicon NPN Triple Diffused Type (PCT process)

2SC5353

Switching Regulator and High Voltage Switching Applications

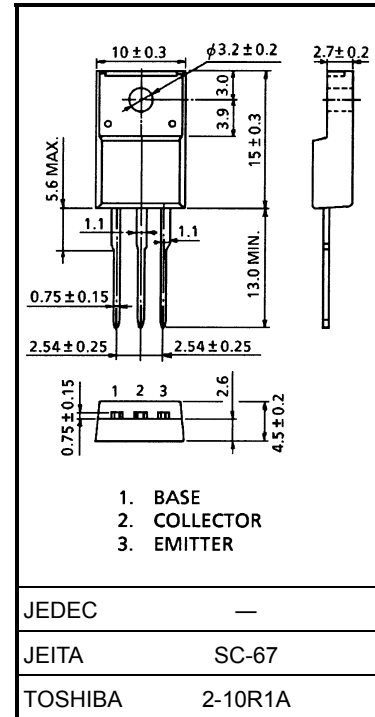
High-Speed DC-DC Converter Applications

- Excellent switching times: $t_r = 0.7 \mu s$ (max), $t_f = 0.5 \mu s$ (max)
- High collectors breakdown voltage: $V_{CEO} = 800 V$

Maximum Ratings ($T_c = 25^\circ C$)

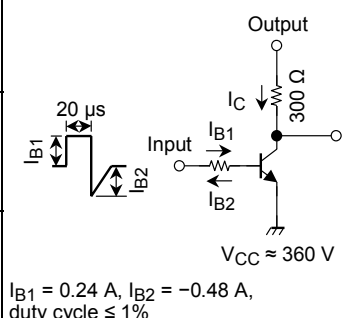
Characteristics		Symbol	Rating	Unit
Collector-base voltage		V_{CBO}	900	V
Collector-emitter voltage		V_{CEO}	800	V
Emitter-base voltage		V_{EBO}	7	V
Collector current	DC	I_C	3	A
	Pulse	I_{CP}	5	
Base current		I_B	1	A
Collector power dissipation	$T_a = 25^\circ C$	P_C	2.0	W
	$T_c = 25^\circ C$		25	
Junction temperature		T_j	150	$^\circ C$
Storage temperature range		T_{stg}	-55 to 150	$^\circ C$

Unit: mm



Weight: 1.7 g (typ.)

Electrical Characteristics (Tc = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current		I_{CBO}	$V_{CB} = 720 \text{ V}, I_E = 0$	—	—	100	μA
Emitter cut-off current		I_{EBO}	$V_{EB} = 7 \text{ V}, I_C = 0$	—	—	10	μA
Collector-base breakdown voltage		$V_{(BR) CBO}$	$I_C = 1 \text{ mA}, I_E = 0$	900	—	—	V
Collector-emitter breakdown voltage		$V_{(BR) CEO}$	$I_C = 10 \text{ mA}, I_B = 0$	800	—	—	V
DC current gain		$h_{FE} (1)$	$V_{CE} = 5 \text{ V}, I_C = 1 \text{ mA}$	10	—	—	
		$h_{FE} (2)$	$V_{CE} = 5 \text{ V}, I_C = 0.15 \text{ A}$	15	—	—	
Collector-emitter saturation voltage		$V_{CE (sat)}$	$I_C = 1.2 \text{ A}, I_B = 0.24 \text{ A}$	—	—	1.0	V
Base-emitter saturation voltage		$V_{BE (sat)}$	$I_C = 1.2 \text{ A}, I_B = 0.24 \text{ A}$	—	—	1.3	V
Switching time	Rise time	t_r	 $I_{B1} = 0.24 \text{ A}, I_{B2} = -0.48 \text{ A},$ duty cycle $\leq 1\%$	—	—	0.7	μs
	Storage time	t_{stg}		—	—	4.0	
	Fall time	t_f		—	—	0.5	

Marking

